



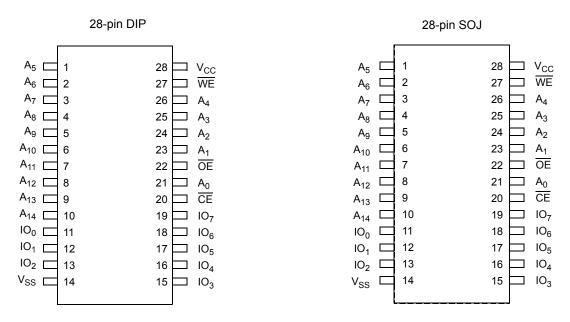
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# **Pin Layout and Specifications**



## **Pin Description**

Pin	Type	Description	DIP	SOJ
A <sub>X</sub>	Input	Address inputs	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 21, 23, 24, 25, 26	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 21, 23, 24, 25, 26
CE	Control	Chip Enable	20	20
IO <sub>X</sub>	Input or Output	Data input outputs	11, 12, 13, 15, 16, 17, 18, 19	11, 12, 13, 15, 16, 17, 18, 19
ŌĒ	Control	Output enable	22	22
V <sub>CC</sub>	Supply	Power (5.0 V)	28	28
$V_{SS}$	Supply	Ground	14	14
WE	Control	Write Enable	27	27

#### Note

<sup>1.</sup> For best practices recommendations, refer to the Cypress application note System Design Guidelines on www.cypress.com.



# **Truth Table**

CE	ŌE	WE	IOx	Mode	Power
Н	Х	Х	High-Z	Deselect/Power-down	Stand by (I <sub>SB</sub> )
L	L	Н	Data Out	Read	Active (I <sub>CC</sub> )
L	Х	L	Data In	Write	Active (I <sub>CC</sub> )
L	Н	Н	High-Z	Selected, Outputs disabled	Active (I <sub>CC</sub> )



# **Maximum Ratings**

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Parameter [2]	Description	Value	Unit
T <sub>STG</sub>	Storage temperature	-65 to +150	°C
T <sub>AMB</sub>	Ambient temperature with power applied (that is, case temperature)	-55 to +125	°C
V <sub>CC</sub>	Core Supply voltage relative to V <sub>SS</sub>	-0.5 to +7.0	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC voltage applied to any pin relative to V <sub>SS</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>OUT</sub>	Output short-circuit current	20	mA
V <sub>ESD</sub>	Static discharge voltage (in accordance with MIL-STD-883, Method 3015)	> 2001	V
I <sub>LU</sub>	Latch-up current	> 200	mA

## **Operating Range**

Range	Ambient Temperature (T <sub>A</sub> ) Voltage Range		
Commercial	0 °C to 70 °C	5.0 V ± 10%	
Industrial	–40 °C to 85 °C	5.0 V ± 10%	

### **DC Electrical Characteristics**

Over the Operating Range

Parameter [2]	Decembries	Condition	Condition		-15	
Parameter 1-3	Description	Condition		Min	Max	Unit
V <sub>IH</sub>	Input HIGH voltage			2.2	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW voltage			-0.5	0.8	V
V <sub>OH</sub>	Output HIGH voltage	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA		2.4	-	V
V <sub>OL</sub>	Output LOW voltage	$V_{CC}$ = Min, $I_{OL}$ = 8.0 mA		-	0.4	V
I <sub>CC</sub>	V <sub>CC</sub> Operating supply current	$V_{CC}$ = Max, $I_{OUT}$ = 0 mA, f = $F_{max}$ = 1/ $t_{RC}$		-	80	mA
I <sub>SB1</sub>	Automatic CE power-down	$Max V_{CC}, \overline{CE} \ge V_{IH},$		-	30	mA
	current – TTL inputs	$V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$ , $f = F_{max}$	L	-	10	mA
I <sub>SB2</sub>	Automatic CE power-down	$Max V_{CC}, \overline{CE} \ge V_{CC} - 0.3 V,$		-	10	mA
	current – CMOS Inputs	$V_{IN} \ge V_{CC} - 0.3 \text{ V, or } V_{IN} \le 0.3 \text{ V, f = 0}$	L	-	500	μА
I <sub>OZ</sub>	Output leakage current	$GND \le V_I \le V_{CC}$ , output disabled		<b>-</b> 5	+5	μΑ
I <sub>IX</sub>	Input leakage current	$GND \le V_I \le V_{CC}$		<b>-</b> 5	+5	μА

#### Note

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<sup>2.</sup>  $V_{IL}$  (min) = -2.0 V for pulse durations of less than 20 ns.



# Capacitance

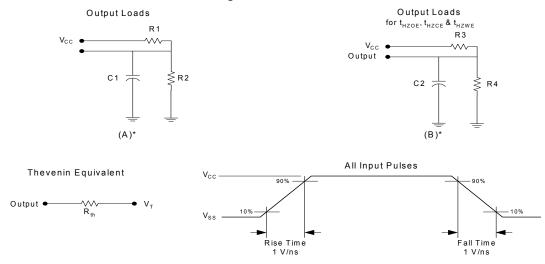
Parameter [3]	Description	Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	$T_A = 25  ^{\circ}\text{C}, f = 1  \text{MHz}, V_{CC} = 5.0  \text{V}$	8	pF
C <sub>OUT</sub>	Output capacitance		8	

### **Thermal Resistance**

Param	neter [3]	Description	Conditions	SOJ	DIP	Unit
$\theta_{JA}$			Still air, soldered on a 3 × 4.5 square inch, two–layer printed circuit board	79	69.33	°C/W
$\theta_{JC}$		Thermal resistance (junction to case)		41.42	31.62	

# **AC Test Loads**

Figure 1. AC Test Loads



<sup>\*</sup> including scope and jig capacitance

## **AC Test Conditions**

Parameter	Description	Nom	Unit
C1	Capacitor 1	30	pF
C2	Capacitor 2	5	
R1	Resistor 1	480	Ω
R2	Resistor 2	255	
R3	Resistor 3	480	
R4	Resistor 4	255	
R <sub>TH</sub>	Resistor Thevenin	167	
$V_{TH}$	Voltage Thevenin	1.73	V

#### Note

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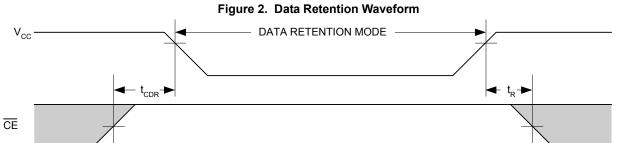
Tested initially and after any design or process change that may affect these parameters.



# **Data Retention Characteristics**

Parameter [4]	Description	Condition	Min	Max	Unit
$V_{DR}$	V <sub>CC</sub> for data retention		2.0	-	V
I <sub>CCDR</sub>	Data retention current	$V_{CC} = V_{DR} = 2.0 \text{ V}, \overline{CE} \ge V_{CC} - 0.3 \text{ V}, \ V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	ı	150	μΑ
ODIN	Chip deselect to data retention time	$V_{\text{IN}} \ge V_{\text{CC}} - 0.3 \text{ V or } V_{\text{IN}} \le 0.3 \text{ V}$	0	-	ns
t <sub>R</sub>	Operation recovery time		200	_	μS

## **Data Retention Waveform**



Note

4. L-version only.



### **AC Electrical Characteristics**

Parameter [5, 6]	Description	-15		1
Parameter [5, 5]		Min	Max	Unit
t <sub>RC</sub>	Read cycle time	15	_	ns
t <sub>AA</sub>	Address to data valid	-	15	ns
t <sub>OHA</sub>	Data hold from address change	3	-	ns
t <sub>ACE</sub>	CE to data valid	-	15	ns
t <sub>DOE</sub>	OE to data valid	-	7	ns
t <sub>LZOE</sub>	OE to Low-Z [7]	0	-	ns
t <sub>HZOE</sub>	OE to High-Z <sup>[7, 8]</sup>	_	7	ns
t <sub>LZCE</sub>	CE to Low-Z [7]	3	-	ns
t <sub>HZCE</sub>	CE to High-Z [7, 8]	_	7	ns
t <sub>PU</sub>	CE to Power-up	0	-	ns
t <sub>PD</sub>	CE to Power-down	_	15	ns
t <sub>WC</sub>	Write Cycle Time [9]	15	-	ns
t <sub>SCE</sub>	CE to write end	10	-	ns
t <sub>AW</sub>	Address setup to write end	10	-	ns
t <sub>HA</sub>	Address hold from write end	0	-	ns
t <sub>SA</sub>	Address setup to write start	0	-	ns
t <sub>PWE</sub>	WE pulse width	9	-	ns
t <sub>SD</sub>	Data setup to write end	9	-	ns
t <sub>HD</sub>	Data hold from write end	0	_	ns
t <sub>HZWE</sub>	WE LOW to High-Z [7, 8]	_	7	ns
t <sub>LZWE</sub>	WE HIGH to Low-Z [7]	3	_	ns

- 5. Test Conditions are based on a transition time of 3 ns or less and timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.

  6. The minimum write cycle pulse width for Write Cycle No. 3 (WE Controlled, OE LOW) should be equal to sum of t<sub>SD</sub> and t<sub>HZWE</sub>.

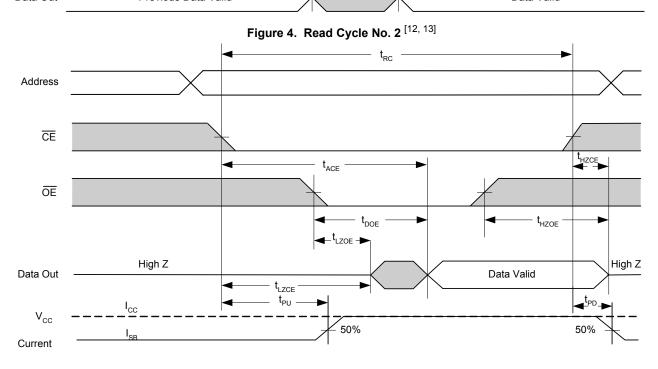
  7. At any given temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZOE</sub> is less than t<sub>LZCE</sub>, and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any given device.

  8. t<sub>HZOE</sub>, t<sub>HZCE</sub>, t<sub>HZWE</sub> are specified as in part (b) of the Figure 1 on page 6.
- 9. The internal memory write time is defined by the overlap of  $\overline{\text{CE}}$  LOW and  $\overline{\text{WE}}$  LOW.  $\overline{\text{CE}}$  and  $\overline{\text{WE}}$  must be LOW to initiate a write, and the transition of any of these signals can terminate the write. The input data setup and hold timing must be referenced to the leading edge of the signal that terminates the write.



# **Timing Waveforms**

Figure 3. Read Cycle No. 1 [10, 11] Address Data Out Data Valid Previous Data Valid



- 10. <u>Device</u> is continuously selected. <u>OE</u> = V<sub>IL</sub> = <u>CE</u>.

  11. <u>WE</u> is HIGH for read cycle.

  12. This cycle is <u>OE</u> controlled and <u>WE</u> is HIGH read cycle.
- 13. Address valid before or similar with  $\overline{\text{CE}}$  transition LOW.



### Timing Waveforms (continued)

Figure 5. Write Cycle No. 1 (WE Controlled) [14, 15, 16]

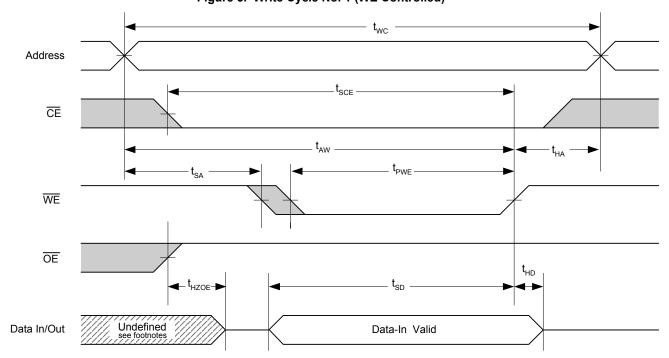
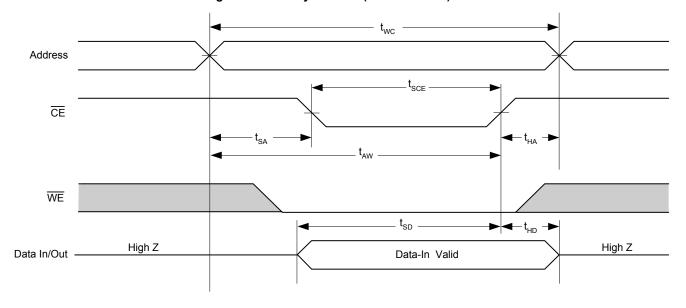


Figure 6. Write Cycle No. 2 ( $\overline{\text{CE}}$  Controlled) [15, 17, 18]



#### Notes

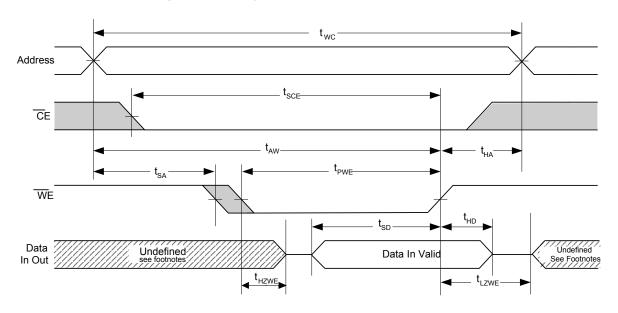
- 14. This cycle is  $\overline{\text{WE}}$  controlled,  $\overline{\text{OE}}$  is HIGH during write.
- 15. Data in and/or out is high impedance if  $\overline{OE} = V_{IH}$ .
- 16. During this  $\underline{\text{period}}$  the IOs are in output state and input signals must not be applied.
- 17. This cycle is  $\overline{\text{CE}}$  controlled.
- 18. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  going HIGH, the output remains in a high impedance state.

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# Timing Waveforms (continued)

Figure 7. Write Cycle No. 3 (WE Controlled, OE LOW) [19]



Note

<sup>19.</sup> The cycle is  $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW. The minimum write cycle time is the sum of  $t_{\text{HZWE}}$  and  $t_{\text{SD}}$ .

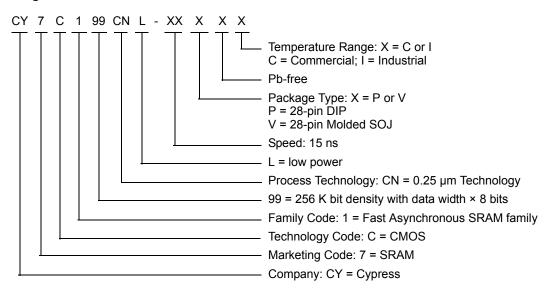


# **Ordering Information**

Contact local sales representative regarding availability of these parts.

Speed (ns)	Ordering Code	Package Diagram		Power Option	Operating Range
15	CY7C199CN-15PXC	51-85014	28-pin DIP (6.9 × 35.6 × 3.5 mm), Pb-free	Standard	Commercial
	CY7C199CNL-15VXI	51-85031	28-pin (300-Mil) Molded SOJ, Pb-free	Low Power	Industrial

### **Ordering Code Definitions**



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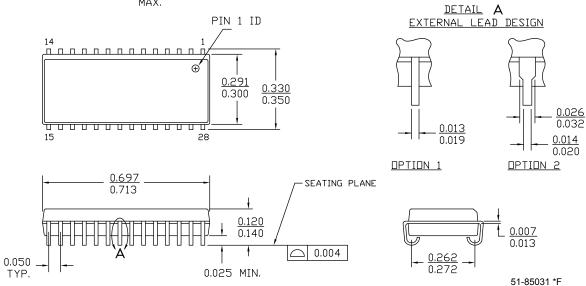
## **Package Diagrams**

### Figure 8. 28-pin SOJ (300 Mils) V28.3 Package Outline, 51-85031

28 Lead (300 Mil) Molded SOJ V21

### NOTE :

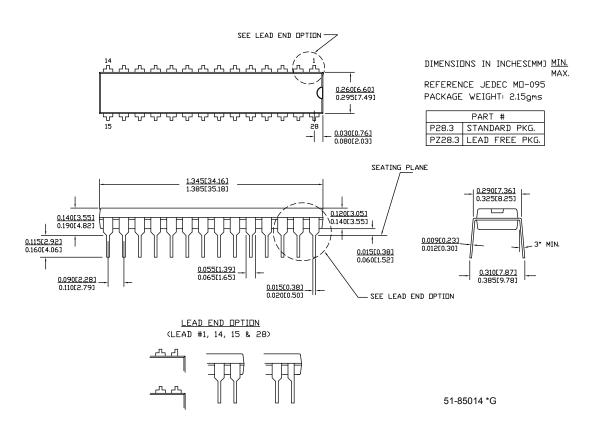
- 1. JEDEC STD REF MD088
- 2. BDDY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE
- 3. DIMENSIONS IN INCHES  $\underline{\text{MIN.}}$  MAX.





# Package Diagrams (continued)

Figure 9. 28-pin PDIP (300 Mils) Package Outline, 51-85014





# Acronyms

Acronym	Description		
CE	Chip Enable		
CMOS Complementary Metal Oxide Semiconductor			
I/O	Input/Output		
OE	Output Enable		
SRAM Static Random Access Memory			
SOJ	Small Outline J-lead		
VFBGA Very Fine-Pitch Ball Grid Array			
WE Write Enable			

## **Document Conventions**

### **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
mA	milliampere			
mV	millivolt			
mW	milliwatt			
ns	nanosecond			
pF	picofarad			
V	volt			
W	watt			

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# **Document History Page**

Revision	ECN	Submission Date	Orig. of Change	Description of Change	
**	430363	See ECN	NXR	New data sheet.	
*A	684342	See ECN	VKN	Added Automotive-A Information Updated Ordering Information Table	
*B	839904	See ECN	VKN	Added t <sub>DOE</sub> spec for Automotive-A part in AC Electrical characteristics table	
*C	2896044	03/19/2010	NXR	Updated Ordering Information Table Updated Package Diagram	
*D	3108898	12/13/2010	PRAS	Added Ordering Code Definitions.	
*E	3198636	03/17/11	PRAS	Dislodged Automotive device information to 001-67737 Updated template and styles.	
*F	3246329	05/04/2011	PRAS	Additional information on ISB1, ISB2 with respect to L parts	
*G	3302830	08/02/2011	RAME	Removed all information related to 28-pin TSOP 1. Removed all information related to 20 ns speed bin. Removed the following parts from ordering information table. CY7C199CN-15VXC CY7C199CN-20ZXI Removed spec 51-85071.	
*H	4318563	03/25/2014	VINI	Updated Package Diagrams: spec 51-85014 – Changed revision from *F to *G. Updated to new template. Completing Sunset Review.	
*	4546472	10/28/2014	VINI	Updated Maximum Ratings: Referred Note 2 in "Parameter" column. Updated AC Electrical Characteristics: Added Note 6 and referred the same note in "Parameter" column.	
*J	4576406	01/16/2015	VINI	Added related documentation hyperlink in page 1. Updated Figure 8 in Package Diagrams (spec 51-85031 *E to *F).	

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